In the Claims:

Please add the following claims:

41. An apparatus for forming a fusing structure to implement redundancy circuits within integrated circuits on a substrate comprising the steps of:

means for forming one or more fuse links of a conductive material above an insulating layer on said substrate with a formation of gates of transistors within said integrated circuits;

means for forming a hard mask layer above said fuse links with a formation of a hard mask layer above said gates;

means for forming sources and drains of the transistors of the integrated circuits; and

means for placing a hard mask removal resist material above the surface of the substrate having openings at said fuse links and said gates; and

means for removing said hard mask on said fuse link simultaneously with removing said hard mask from said gates.

42. The apparatus of claim 41 further comprising:

means for forming interlayer dielectric above the surface of the substrate; and

means for forming self-aligned contacts to the sources and drains of the integrated circuits; and

means for forming an opening above the fuse links.

43. The apparatus of claim 41 wherein said conductive material is selected from a group of conductive materials consisting of metals, heavily doped polycrystalline silicon, and alloys of metals and heavily doped polycrystalline silicon.

44. The apparatus of claim 41 wherein said insulating layer above which said fuse links are formed is a field oxide.

45. The apparatus of claim 41 wherein said redundancy circuit is a column of a DRAM array.

46. The apparatus of claim 41 wherein said redundancy circuit is a row of a DRAM array.

47. The apparatus of claim 41 wherein the opening in the interlayer dielectric is formed such that said interlayer dielectric between a bottom portion of said opening and said fuse links are transparent to allow destruction of said fuse links.

48. The apparatus of claim 41 wherein said hard mask on said fuse links are a thickness that allows reliable destruction of said fuse links.